**Product data sheet** 

## 1. General description

Planar passivated AC Thyristor Triac power switch in a SOT186A (TO-220F) "full pack" plastic package with self-protective capabilities against low and high energy transients.

### 2. Features and benefits

- Clamping structure ensuring safe high over-voltage withstand capability
- Full cycle AC conduction
- Isolated mounting base package
- Less sensitive gate for high noise immunity
- Over-voltage withstand capability to IEC 61000-4-5
- Pin compatible with standard triacs
- Planar passivated for voltage ruggedness and reliability
- Safe clamping capability for low energy over-voltage transients
- Self-protective turn-on during high energy voltage transients
- · Triggering in three quadrants only
- Very high immunity to false turn-on by dV/dt

## 3. Applications

- AC fan, pump and compressor controls
- Highly inductive, resistive and safety loads
- Large and small appliances (White Goods)
- Reversing induction motor controls
- Applications subject to high temperature

#### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{DRM}$	repetitive peak off- state voltage		-	-	800	V
I <sub>TSM</sub>	non-repetitive peak on- state current	full sine wave; $T_{j(init)} = 25 ^{\circ}C$ ; $t_p = 20  \text{ms}$ ; Fig. 4; Fig. 5	-	-	120	Α
T <sub>j</sub>	junction temperature		-	-	125	°C
I <sub>T(RMS)</sub>	RMS on-state current	full sine wave; $T_h \le 57$ °C; Fig. 1; Fig. 2; Fig. 3	-	-	12	Α





Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$V_{PP}$	peak pulse voltage	T <sub>j</sub> = 25 °C; non-repetitive, off-state; Fig. 6		-	-	2	kV
Static char	acteristics						
I <sub>GT</sub>	gate trigger current	$V_D = 12 \text{ V; } I_T = 100 \text{ mA; LD+ G+;}$ $T_j = 25 \text{ °C; } Fig. 8$		-	-	35	mA
		$V_D = 12 \text{ V; } I_T = 100 \text{ mA; LD+ G-;}$ $T_j = 25 \text{ °C; } Fig. 8$		-	-	35	mA
		$V_D = 12 \text{ V; } I_T = 100 \text{ mA; LD- G-;}$ $T_j = 25 \text{ °C; } Fig. 8$		-	-	35	mA
$V_{CL}$	clamping voltage	$I_{CL}$ = 0.1 mA; $t_p$ = 1 ms; $T_j$ = 25 °C		850	-	-	V
Dynamic cl	haracteristics						
dV <sub>D</sub> /dt	rate of rise of off-state voltage	V <sub>DM</sub> = 536 V; T <sub>j</sub> = 125 °C; exponential 3000 waveform; gate open circuit			-	-	V/µs
dI <sub>com</sub> /dt	rate of change of commutating current	$V_D$ = 400 V; $T_j$ = 125 °C; $I_{T(RMS)}$ = 12 A; $dV_{com}/dt$ = 20 V/ $\mu$ s; (snubberless condition); gate open circuit		14	-	-	A/ms

# 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1	mb	T2—T1
2	T2	main terminal 2		G sym051
3	G	gate		·
mb	n.c.	mounting base; isolated		
			TO-220F (SOT186A)	

# 6. Ordering information

Table 3. Ordering information

Type number	Package							
	Name	Description	Version					
ACTT12X-800C	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-220 "full pack"	SOT186A					

ACTT12X-800C

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**AC Thyristor Triac power switch** 

# 7. Marking

### Table 4. Marking codes

Type number	Marking code
ACTT12X-800C	ACTT12X-800C

# 8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DRM}$	repetitive peak off-state voltage		-	800	V
I <sub>T(RMS)</sub>	RMS on-state current	full sine wave; $T_h \le 57$ °C; Fig. 1; Fig. 2; Fig. 3	-	12	Α
I <sub>TSM</sub>	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25 \text{ °C}$ ; $t_p = 20 \text{ ms}$ ; Fig. 4; Fig. 5	-	120	A
		full sine wave; $T_{j(init)} = 25 \text{ °C}$ ; $t_p = 16.7 \text{ ms}$	-	132	А
I <sup>2</sup> t	I <sup>2</sup> t for fusing	t <sub>p</sub> = 10 ms; sine-wave pulse	-	72	A <sup>2</sup> s
dl <sub>T</sub> /dt	rate of rise of on-state current	$I_T$ = 12 A; $I_G$ = 0.2 A; $dI_G/dt$ = 0.2 A/ $\mu$ s	-	100	A/µs
I <sub>GM</sub>	peak gate current	t = 20 μs	-	2	Α
P <sub>GM</sub>	peak gate power		-	5	W
P <sub>G(AV)</sub>	average gate power	over any 20 ms period	-	0.5	W
T <sub>stg</sub>	storage temperature		-40	150	°C
Tj	junction temperature		-	125	°C
$V_{PP}$	peak pulse voltage	T <sub>j</sub> = 25 °C; non-repetitive, off-state; Fig. 6	-	2	kV

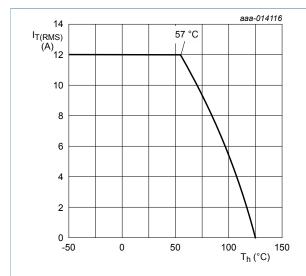


Fig. 1. RMS on-state current as a function of heatsink temperature; maximum values

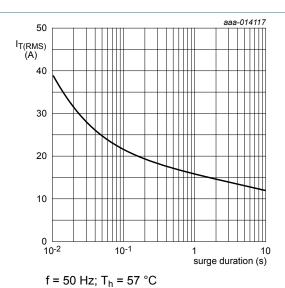


Fig. 2. RMS on-state current as a function of surge duration; maximum values

### **AC Thyristor Triac power switch**

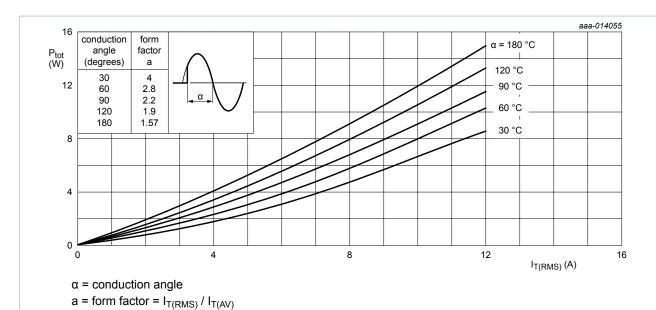


Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values

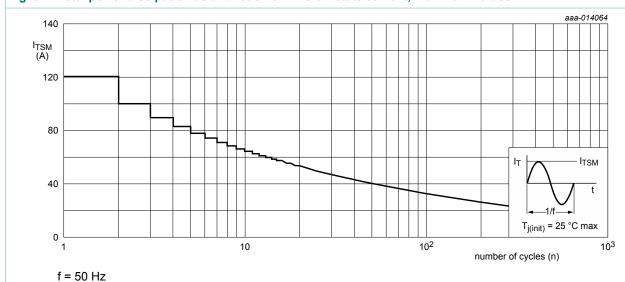


Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

### **AC Thyristor Triac power switch**

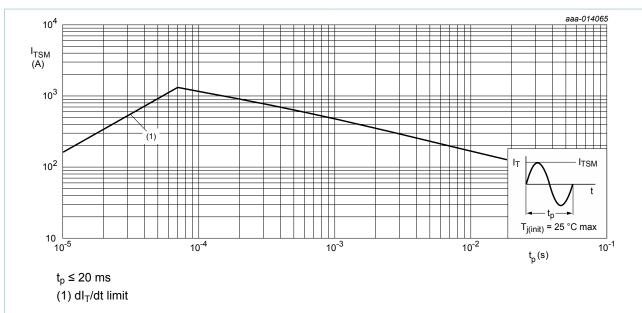


Fig. 5. Non-repetitive peak on-state current as a function of pulse width; maximum values

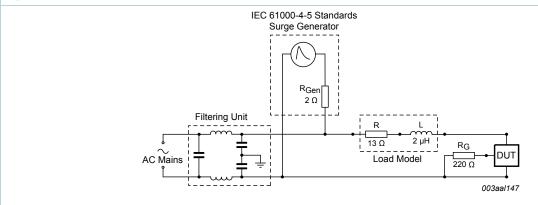
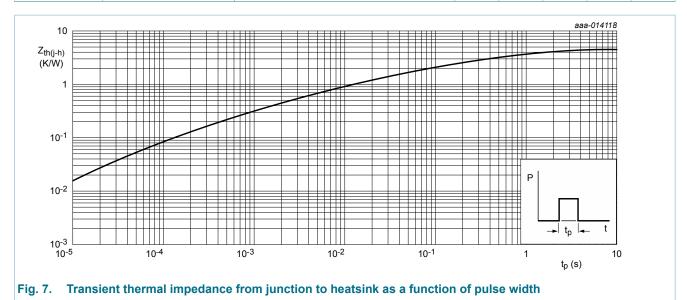


Fig. 6. Test circuit for inductive and resistive loads with conditions equivalent to IEC 61000-4-5

# 9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-h)</sub>	thermal resistance from junction to heatsink	full cycle; with heatsink compound; Fig. 7		-	-	4.5	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air		-	55	-	K/W



## 10. Isolation characteristics

Table 7. Isolation characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>isol(RMS)</sub>	RMS isolation voltage	50 Hz $\leq$ f $\leq$ 60 Hz; RH $\leq$ 65% RH; T <sub>h</sub> = 25 °C; from all terminals to external heatsink; sinusoidal waveform; clean and dust free	-	-	2500	V	
C <sub>isol</sub>	isolation capacitance	f = 1 MHz; T <sub>h</sub> = 25 °C; from main terminal 2 to external heatsink		-	10	-	pF

# 11. Characteristics

#### Table 8. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	acteristics					
I <sub>GT</sub>	gate trigger current	$V_D = 12 \text{ V; } I_T = 100 \text{ mA; LD+ G+;}$ $T_j = 25 \text{ °C; } Fig. 8$	-	-	35	mA
		$V_D = 12 \text{ V; } I_T = 100 \text{ mA; LD+ G-;}$ $T_j = 25 \text{ °C; } Fig. 8$	-	-	35	mA
		$V_D$ = 12 V; $I_T$ = 100 mA; LD- G-; $T_j$ = 25 °C; <u>Fig. 8</u>	-	-	35	mA
I <sub>L</sub> latching current	latching current	$V_D = 12 \text{ V}; I_G = 100 \text{ mA}; LD+ G+;$ $T_j = 25 \text{ °C}; Fig. 9$	-	-	50	mA
		$V_D = 12 \text{ V; } I_G = 100 \text{ mA; LD+ G-;}$ $T_j = 25 \text{ °C; } Fig. 9$	-	-	70	mA
		$V_D = 12 \text{ V}; I_G = 100 \text{ mA}; \text{LD- G-};$ $T_j = 25 ^{\circ}\text{C}; \text{Fig. 9}$	-	-	50	mA
I <sub>H</sub>	holding current	V <sub>D</sub> = 12 V; T <sub>j</sub> = 25 °C; <u>Fig. 10</u>	-	-	50	mA
V <sub>T</sub>	on-state voltage	I <sub>T</sub> = 17 A; T <sub>j</sub> = 25 °C; <u>Fig. 11</u>	-	1.25	1.5	V
$V_{GT}$	gate trigger voltage	V <sub>D</sub> = 12 V; I <sub>T</sub> = 100 mA; T <sub>j</sub> = 25 °C; Fig. 12	-	0.8	1	V
		V <sub>D</sub> = 400 V; I <sub>T</sub> = 100 mA; T <sub>j</sub> = 125 °C; Fig. 12	0.2	0.45	-	V
I <sub>D</sub>	off-state current	V <sub>D</sub> = 800 V; T <sub>j</sub> = 25 °C	-	-	10	μΑ
		V <sub>D</sub> = 800 V; T <sub>j</sub> = 125 °C	-	-	0.5	mA
V <sub>CL</sub>	clamping voltage	I <sub>CL</sub> = 0.1 mA; t <sub>p</sub> = 1 ms; T <sub>j</sub> = 25 °C	850	-	-	V
Dynamic cl	naracteristics		l			
dV <sub>D</sub> /dt	rate of rise of off-state voltage	$V_{\rm DM}$ = 536 V; T <sub>j</sub> = 125 °C; exponential 3000 waveform; gate open circuit		-	-	V/µs
dl <sub>com</sub> /dt	rate of change of commutating current	$V_D$ = 400 V; $T_j$ = 125 °C; $I_{T(RMS)}$ = 12 A; $dV_{com}/dt$ = 20 V/ $\mu$ s; (snubberless condition); gate open circuit	14	-	-	A/ms

### **AC Thyristor Triac power switch**

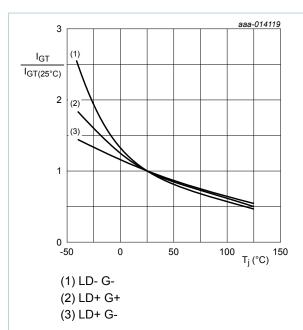


Fig. 8. Normalized gate trigger current as a function of junction temperature

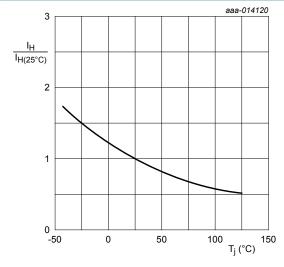


Fig. 10. Normalized holding current as a function of junction temperature

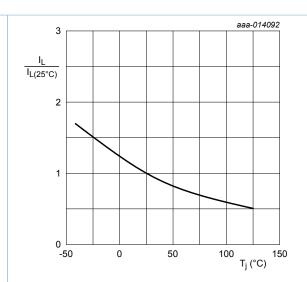
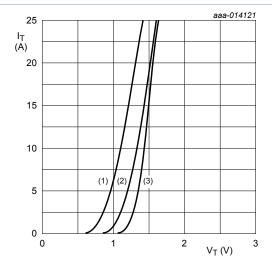


Fig. 9. Normalized latching current as a function of junction temperature



 $V_0 = 1.025 \text{ V}; R_s = 0.028 \Omega$ 

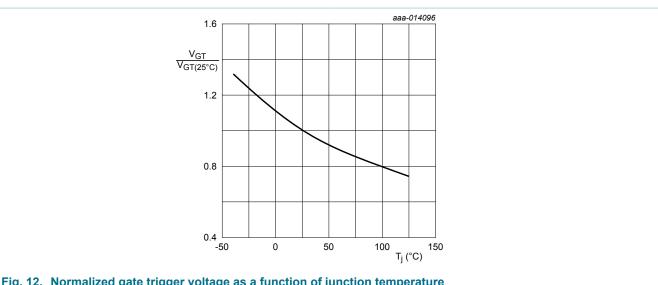
(1) T<sub>i</sub> = 125 °C; typical values

(2) T<sub>i</sub> = 125 °C; maximum values

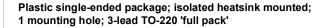
(3) T<sub>i</sub> = 25 °C; maximum values

Fig. 11. On-state current as a function of on-state voltage

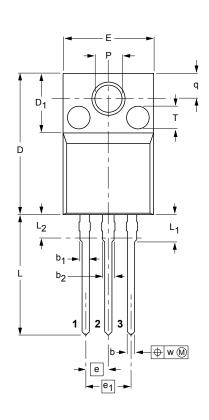
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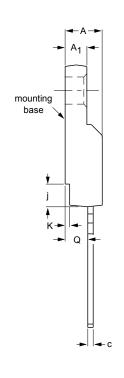


# 12. Package outline



SOT186A





0 5 10 mm

#### DIMENSIONS (mm are the original dimensions)

UNIT	Α	A <sub>1</sub>	b	b <sub>1</sub>	b <sub>2</sub>	С	D	D <sub>1</sub>	E	е	e <sub>1</sub>	j	K	L	L <sub>1</sub>	L <sub>2</sub> <sup>(1)</sup> max.	Р	Q	q	T <sup>(2)</sup>	w
mm	4.6 4.0	2.9 2.5	0.9 0.7	1.1 0.9	1.4 1.0	0.7 0.4	15.8 15.2	6.5 6.3	10.3 9.7	2.54	5.08	2.7 1.7	0.6 0.4	14.4 13.5	3.30 2.79	3	3.2 3.0	2.6 2.3	3.0 2.6	2.5	0.4

#### Notes

- 1. Terminal dimensions within this zone are uncontrolled.
- 2. Both recesses are #  $2.5 \times 0.8$  max. depth

OUTLINE		REFER	EUROPEAN	ISSUE DATE			
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE	
SOT186A		3-lead TO-220F				<del>02-04-09</del> 06-02-14	

Fig. 13. Package outline TO-220F (SOT186A)

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